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Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-14. (Canceled)

15. (Currently amended) A semiconductor device comprising:

a substrate, and

a multilayer formed on the substrate, the multilayer

comprising a plurality of semiconductor elements and a plurality of dummy semiconductor elements, and

a semiconductor element area on the substrate, which includes a the plurality of the semiconductor elements, and ~~a dummy area on the substrate, which includes a plurality of the dummy semiconductor elements~~, the semiconductor element area being surrounded by ~~the dummy area~~ the plurality of dummy semiconductor elements,

wherein each of the plurality of semiconductor elements includes a capacitor which is comprised of a bottom electrode, a first dielectric layer on the bottom electrode and a top electrode on the first dielectric layer, and the first dielectric layer is composed of a material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material,

wherein each of the plurality of dummy semiconductor elements includes a dummy capacitor which is comprised of a dummy bottom electrode, a second dielectric layer on the dummy bottom electrode and a dummy top electrode on the second dielectric layer, and the second dielectric layer is composed of a material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material,

wherein each of the plurality of dummy semiconductor elements is located so that a space between the electrode and the dummy electrode is in a predetermined range, and

wherein the multilayer is produced by a method comprising:

forming a dielectric film for the first dielectric layer and the second dielectric layer;

forming an electrically conductive film on the dielectric film;

and

etching the electrically conductive film so as to form the electrode and the dummy electrode.

16. (Previously presented) A semiconductor device according to claim 15, wherein the predetermined range of the space is between $0.3\mu\text{m}$ and $14\mu\text{m}$.
17. (Previously presented) A semiconductor device according to claim 15, wherein remnant polarization in the capacitor is in the range of 13 to $15\mu\text{C}/\text{cm}^2$.
18. (Previously presented) A semiconductor device according to claim 15, wherein the first dielectric layer and the second dielectric layer are composed of a material selected from $\text{SrBi}_x\text{Ta}_x\text{O}_y$, $\text{Ba}_x\text{Sr}_{1-x}\text{TiO}_x$, $\text{Pb}(\text{Zr}_{1-x}\text{Ti}_x)\text{O}_3$, $\text{SrBi}_2(\text{Ta}_{1-x}\text{Nb}_x)_2\text{O}_9$ or $\text{Bi}_4\text{Ti}_3\text{O}_{12}$, where $0 \leq x \leq 1$.